

AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions, and listings, of claims in the application.

1. (Currently Amended) A method for burying a resist comprising:
forming an interlayer film on a substrate;
forming an opening in said interlayer film;
applying a resist film to said interlayer film, including said opening; and
patterning said resist film substantially in the same form as said opening by exposing said resist with a photomask having a light-shielding portion or a light-transmitting portion substantially in the same form as said opening and developing said resist to remove said resist other than the resist in the opening, thereby burying said resist film inside of said opening.

2. (Currently Amended) A method for burying a resist comprising:
forming an interlayer film on a substrate;
forming an opening in said interlayer film;
forming a second film on said interlayer film including said opening;
applying a resist film to said second film; and
patterning said resist film substantially in the same form as said opening by exposing said resist with a photomask having a light-shielding portion or a light-transmitting portion substantially in the same form as said opening and developing said resist to remove said resist other than the resist in the opening, thereby burying said resist film inside of said opening.

3. (Previously Presented) The method for burying a resist according to claim 1, wherein said resist is positive resist and including patterning said resist with a photomask having a light-shielding portion smaller in area than said opening.

4. (Previously Presented) The method for burying a resist according to claim 2, wherein said resist is a positive resist and including patterning said resist with a photomask having a light-shielding portion smaller in area than said opening.

5. (Previously Presented) The method for burying a resist according to claim 1, wherein said resist is a negative resist and including patterning said resist with a photomask having a light-transmitting portion smaller in area than said opening.

6. (Previously Presented) The method for burying a resist according to claim 2, wherein said resist is a negative resist and including patterning said resist with a photomask having a light-transmitting portion smaller in area than said opening.

7. (Currently Amended) A method for manufacturing a semiconductor device comprising:

forming an interlayer film on a substrate;

forming an opening in said interlayer film;

applying a resist film to said interlayer film, including said opening;

patterning said resist film substantially in the same form as said opening by exposing said resist with a photomask having a light-shielding portion or a light-transmitting portion substantially in the same form as said opening and developing said resist to remove said resist other than the resist in the opening, thereby burying said resist film in said opening; and

etching said interlayer film while masking a bottom portion of said opening with said resist film buried in said opening.

8. (Currently Amended) A method for manufacturing a semiconductor device comprising:

forming an interlayer film on a substrate;

forming an opening in said interlayer film;

applying a second film on said interlayer film, including said opening;

applying a resist film on said second film; and

patterning said resist film substantially in the same form as said opening by exposing said resist with a photomask having a light-shielding portion or a light-transmitting portion substantially in the same form as said opening and developing said resist to remove said resist other than the resist in the opening, thereby burying said resist film in said opening; and

etching said second film while masking a bottom portion of said opening with said resist film buried in said opening.

Claims 9-12 (Cancelled).